2N4125TFR Datasheet

DiGi Electronics Part Number	2N4125TFR-DG
Manufacturer	onsemi
Manufacturer Product Number	2N4125TFR
Description	TRANS PNP 30V 0.2A TO92-3
Detailed Description	Bipolar (BJT) Transistor PNP 30 V 200 mA 625 mW T hrough Hole TO-92-3

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RFQ Email: Info@DiGi-Electronics.com

Purchase and inquiry

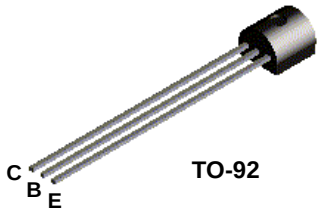
Manufacturer Product Number:	Manufacturer:
2N4125TFR	onsemi
Series:	Product Status:
-	Obsolete
Transistor Type:	Current - Collector (Ic) (Max):
PNP	200 mA
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ Ib, Ic:
30 V	400mV @ 5mA, 50mA
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ Ic, Vce:
50nA (ICBO)	50 @ 2mA, 1V
Power - Max:	Frequency - Transition:
625 mW	-
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Through Hole
Package / Case:	Supplier Device Package:
TO-226-3, TO-92-3 (TO-226AA) Formed Leads	TO-92-3
Base Product Number:	
2N4125	

Environmental & Export classification

Moisture Sensitivity Level (MSL):	REACH Status:
1 (Unlimited)	REACH Unaffected
ECCN:	HTSUS:
EAR99	8541.21.0095

FAIRCHILD
SEMICONDUCTOR TM

2N4125



TO-92

PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents of 10 μA to 100 mA.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CEO}	Collector-Emitter Voltage	30	V
V_{CBO}	Collector-Base Voltage	30	V
V_{EBO}	Emitter-Base Voltage	4.0	V
I_C	Collector Current - Continuous	200	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:
1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N4125	
P_D	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

PNP General Purpose Amplifier

(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

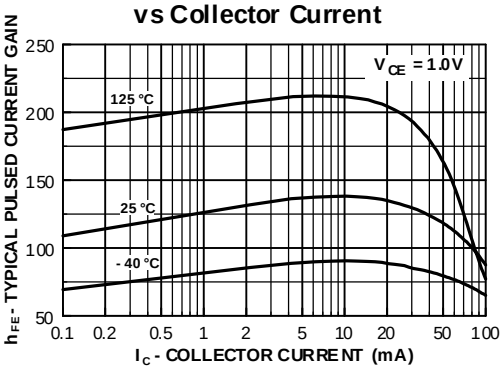
Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHARACTERISTICS					
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	I_C = 1.0 mA, I_B = 0	30		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	I_C = 10 μA, I_E = 0	30		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	I_E = 10 μA, I_C = 0	4.0		V
I_{CBO}	Collector-Cutoff Current	V_{CB} = 20 V, I_E = 0		50	nA
I_{EBO}	Emitter-Cutoff Current	V_{EB} = 3.0 V, I_C = 0		50	nA
ON CHARACTERISTICS*					
h_{FE}	DC Current Gain	V_{CE} = 1.0 V, I_C = 2.0 mA V_{CE} = 1.0 V, I_C = 50 mA	50 25	150	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C = 50 mA, I_B = 5.0 mA		0.4	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C = 50 mA, I_B = 5.0 mA		0.95	V
SMALL SIGNAL CHARACTERISTICS					
C_{ob}	Output Capacitance	V_{CB} = 5.0 V, f = 100 kHz		4.5	pF
C_{ib}	Input Capacitance	V_{BE} = 0.5 V, f = 100 kHz		10	pF
h_{fe}	Small-Signal Current Gain	I_C = 2.0 mA, V_{CE} = 10 V, f = 1.0 kHz I_C = 10 mA, V_{CE} = 20 V, f = 100 MHz	50 2.0	200	
NF	Noise Figure	V_{CE} = 5.0 V, I_C = 100 μA, R_S = 1.0 kΩ, f = 10Hz to 15.7 kHz,		5.0	dB

*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

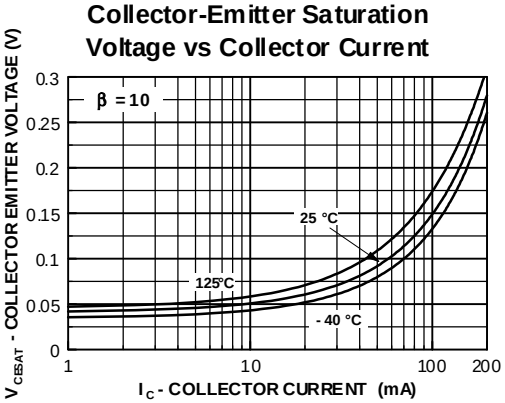
PNP General Purpose Amplifier
(continued)

Typical Characteristics

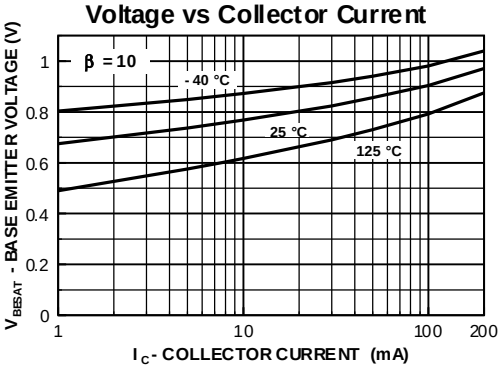
Typical Pulsed Current Gain vs Collector Current



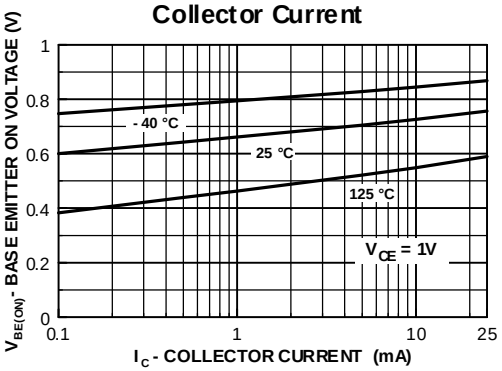
Collector-Emitter Saturation Voltage vs Collector Current



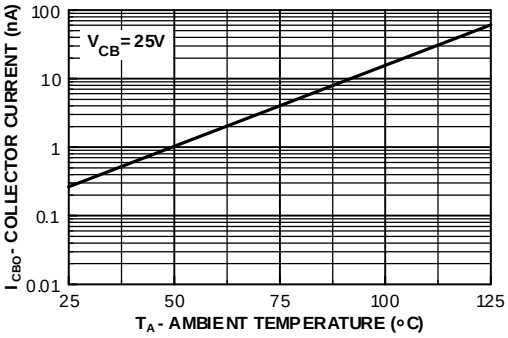
Base-Emitter Saturation Voltage vs Collector Current



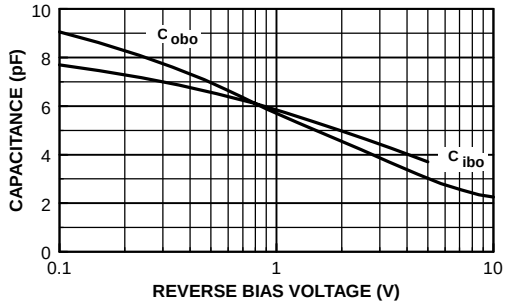
Base Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature

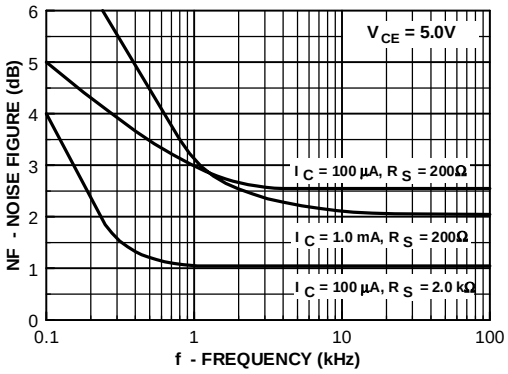


Common-Base Open Circuit Input and Output Capacitance vs Reverse Bias Voltage

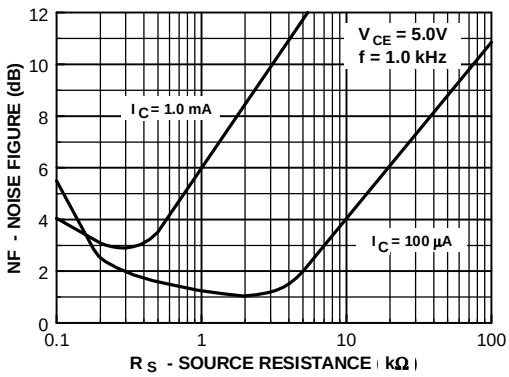


Typical Characteristics (continued)

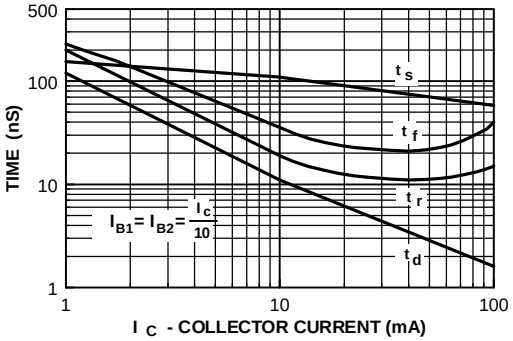
Noise Figure vs Frequency



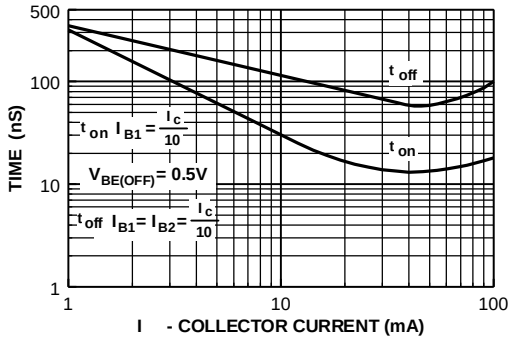
Noise Figure vs Source Resistance



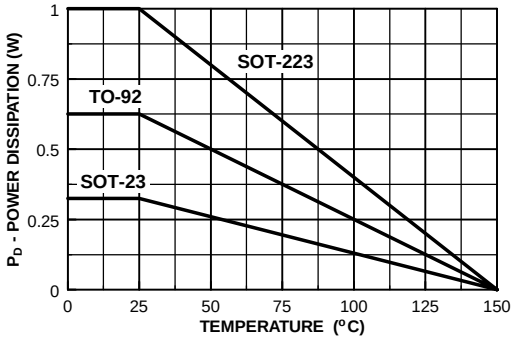
Switching Times vs Collector Current



Turn On and Turn Off Times vs Collector Current

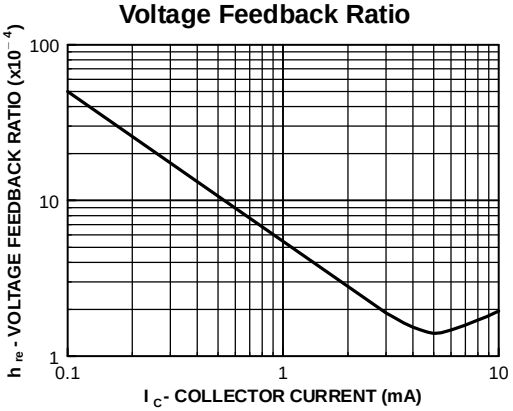


Power Dissipation vs Ambient Temperature

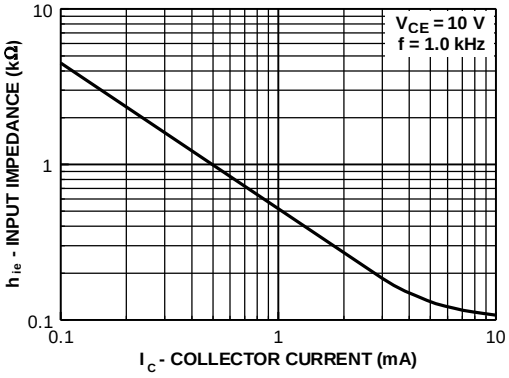


Typical Characteristics (continued)

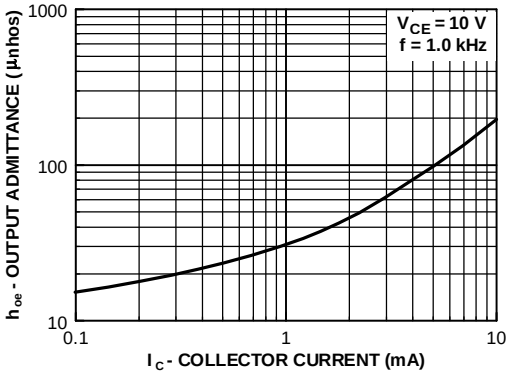
Voltage Feedback Ratio



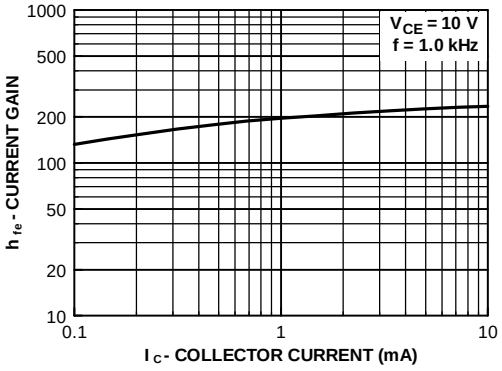
Input Impedance



Output Admittance



Current Gain



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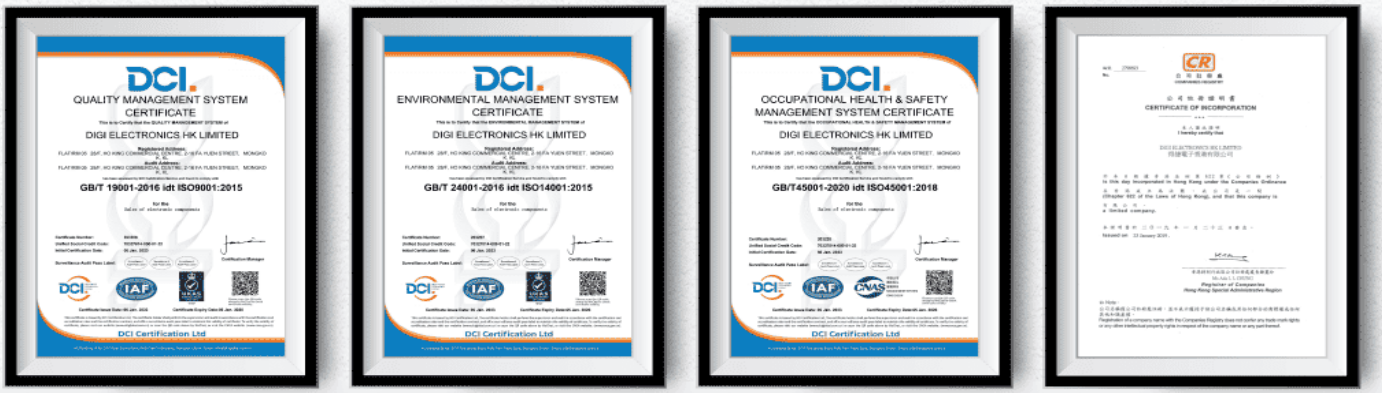

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